STRUCTURE Silicon Monolithic Integrated Circuit

NAME OF PRODUCT DC-AC Inverter Control IC

TYPE **BD9888F、BD9888FV**

FUNCTION
- 2ch control with Push-Pull
- Lamp current and voltage sense feed back control
- Sequencing easily achieved with Soft Start Control
- Short circuit protection with Timer Latch
- Under Voltage Lock Out
- Short circuit protection with over voltage
- Mode-selectable the operating or stand-by mode by stand-by pin
- Synchronous operating the other BD9888F or BD9888FV IC's
- BURST mode controlled by PWM and DC input
- Short circuit protection with voltage difference detection

○Absolute Maximum Ratings (Ta = 25℃)

Parameter	Symbol	Limits	Unit
Supply Voltage	VCC	15	V
Operating Temperature Range	Topr	-40～+90	℃
Storage Temperature Range	Tstg	-55～+125	℃
Power Dissipation	Pd	600*1(BD9888F)	mW
		850*2(BD9888FV)	
Maximum Junction Temperature	Tjmax	+125	℃

*1Pd derate at 6.0mW/℃ for temperature above Ta = 25℃ (When mounted on a PCB 70.0mm×70.0mm×1.6mm)
*2Pd derate at 8.5mW/℃ for temperature above Ta = 25℃ (When mounted on a PCB 70.0mm×70.0mm×1.6mm)

○Recommended operating condition

Parameter	Symbol	Limits	Unit
Supply voltage	VCC	5.0～14.0	V
CT oscillation frequency	fCT	20～150	kHz
BCT oscillation frequency	fBCT	0.05～0.50	kHz

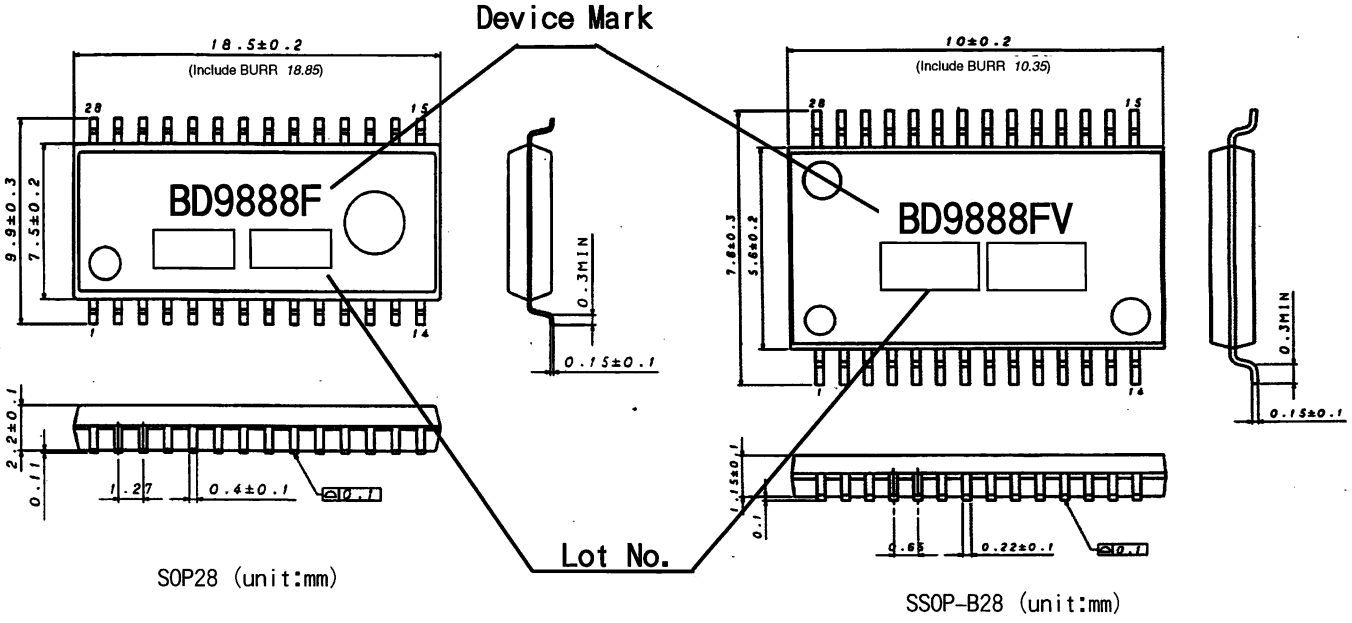
Status of this document
The Japanese version of this document is the official specification.
Please use the translation version of this document as a reference to expedite understanding of the official version.
If these are any uncertainty in translation version of this document, official version takes priority.

○Electric Characteristics (Ta=25℃, VCC=7V)

Parameter	Symbol	Limits			Unit	Conditions
		MIN.	TYP.	MAX.		
((WHOLE DEVICE))						
Operating current	Icc1	—	11.0	17.0	mA	CT=0.5V
Stand-by current	Icc2	—	2	10	μA	
((OVER VOLTAGE DETECT))						
FB over voltage detect voltage	Vovf	2.20	2.40	2.60	V	
((STAND BY CONTROL))						
Stand-by voltage H	VstH	1.6	—	VCC	V	System O N
Stand-by voltage L	VstL	-0.3	—	0.8	V	System O F F
Stand-by hysteresis	⊿Vst	0.08	0.18	0.28	V	
((TIMER LATCH))						
Timer Latch voltage	Vcp	1.9	2.0	2.1	V	
Timer Latch current	Icp	0.5	1.0	1.5	μA	
((BURST MODE))						
BOSC Max voltage	VburH	1.94	2.0	2.06	V	f_{BCT}=0.2kHz
BOSC Min Voltage	VburL	0.4	0.5	0.6	V	f_{BCT}=0.2kHz
BOSC constant current	IBCT	1.35/BRT	1.5/BRT	1.65/BRT	A	
BOSC frequency	fBCT	266	280	294	Hz	BRT=33kΩ、BCT=0.050μF
((OSC BLOCK))						
OSC constant current	ICT	1.35/RT	1.5/RT	1.65/RT	A	
OSC Max voltage	VoscH	1.8	2.0	2.2	V	f_{CT}=60kHz
OSC Min voltage	VoscL	0.3	0.5	0.7	V	f_{CT}=60kHz
MAX DUTY	MAXDUTY	44	46.5	49	%	f_{CT}=60kHz
Soft start current	Iss	1.0	2.0	3.0	μA	
IS COMP detect Voltage	Visc	0.45	0.50	0.55	V	
SS COMP detect voltage	Vss	2.0	2.2	2.4	V	
SRT ON resistance	RSRT	—	200	400	Ω	
((UVLO BLOCK))						
Operating voltage	VuvloH	4.100	4.300	4.500	V	
Shut down voltage	VuvloL	3.900	4.100	4.300	V	
((REG BLOCK))						
REG output voltage	VREG	3.038	3.100	3.162	V	
REG source current	IREG	5.0	—	—	mA	
VREF voltage	VREF	1.225	1.250	1.275	V	VREF=Open
((FEED BACK BLOCK))						
IS threshold voltage	Vis	1.225	1.250	1.275	V	
VS threshold voltage	Vvs	1.220	1.250	1.280	V	
IS source current 1	Iis1	—	—	1.5	μA	DUTY=2.0V
IS source current 2	Iis2	13.0	20.0	27.0	μA	DUTY=0V、IS=0.5V
VS source current	Ivs	—	—	1.0	μA	
((OUTPUT BLOCK))						
NAch output voltage H	VoutNAH	VCC-0.3	VCC-0.1	—	V	
NBch output voltage H	VoutNBH	VCC-0.3	VCC-0.1	—	V	
NAch output voltage L	VoutNAL	—	0.1	0.3	V	
NBch output voltage L	VoutNBL	—	0.1	0.3	V	
NAch output sink resistance	RsinkNA	—	5	10	Ω	Isink = 10mA
NAch output source resistance	RsourceNA	—	8	16	Ω	Isource = 10mA
NBch output sink resistance	RsinkNB	—	5	10	Ω	Isink = 10mA
NBch output source resistance	RsourceNB	—	8	16	Ω	Isource = 10mA
Drive output frequency	fOUT	58.5	60.0	61.5	KHz	RT=18kΩ、CT=395pF
((COMP BLOCK))						
Under voltage detect	VCOMPL	0.620	0.640	0.660	V	
Voltage difference detect	⊿VCOMP	0.40	0.45	0.5	V	|VCOMPA-VCOMPB|

(This product is not designed to be radiation-resistant.)

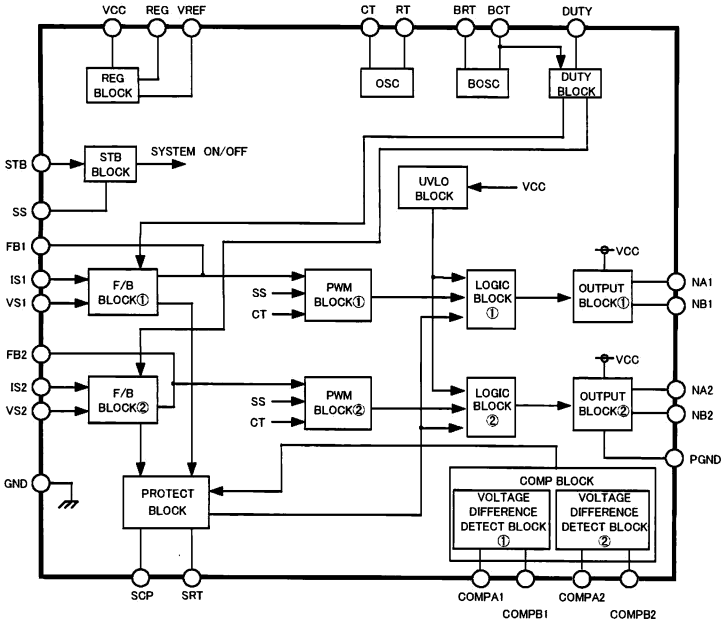
○Package Dimensions



SOP28 (unit:mm)

SSOP-B28 (unit:mm)

○Block Diagram



○Pin Description

Pin No.	Pin Name	Function
1	DUTY	Control PWM mode and BURST mode
2	BRT	External resistor from BRT to GND for adjusting the BURST triangle oscillator
3	BCT	External capacitor from BCT to GND for adjusting the BURST triangle oscillator
4	RT	External resistor from SRT to RT for adjusting the triangle oscillator
5	SRT	External resistor from SRT to RT for adjusting the triangle oscillator
6	CT	External capacitor from CT to GND for adjusting the triangle oscillator
7	GND	GROUND
8	FB1	Error amplifier output①
9	IS1	Error amplifier input①
10	VS1	Error amplifier input②
11	FB2	Error amplifier output②
12	IS2	Error amplifier input③
13	VS2	Error amplifier input④
14	VREF	Reference voltage
15	COMPA1	Voltage difference or under voltage detect for 1ch
16	STB	Stand-by switch
17	COMPB1	Voltage difference or under voltage detect for 1ch
18	COMPA2	Voltage difference or under voltage detect for 2ch
19	COMPB2	Voltage difference or under voltage detect for 2ch.
20	REG	Internal regulator output
21	SS	External capacitor from SS to GND for Soft Start Control
22	SCP	External capacitor from SCP to GND for Timer Latch
23	NA2	FET driver for 2ch
24	NB2	FET driver for 2ch
25	PGND	Ground for FET drivers
26	NB1	FET driver for 1ch
27	NA1	FET driver for 1ch
28	Vcc	Supply voltage input

○NOTE FOR USE

1. When designing the external circuit, including adequate margins for variation between external devices and IC. Use adequate margins for steady state and transient characteristics.
2. The circuit functionality is guaranteed within of ambient temperature operation range as long as it is within recommended operating range. The standard electrical characteristic values cannot be guaranteed at other voltages in the operating ranges, however the variation will be small.
3. Mounting failures, such as misdirection or miscounts, may harm the device.
4. A strong electromagnetic field may cause the IC to malfunction.
5. The GND pin should be the location within ±0.3V compared with the PGND pin.
6. BD9888F and BD9888FV incorporate a built-in thermal shutdown circuit (TSD circuit). The thermal shutdown circuit (TSD circuit) is designed only to shut the IC off to prevent runaway thermal operation. It is not designed to protect the IC or guarantee its operation of the thermal shutdown circuit is assumed.
7. Absolute maximum ratings are those values that, if exceeded, may cause the life of a device to become significantly shortened. Moreover, the exact failure mode caused by short or open is not defined. Physical countermeasures, such as a fuse, need to be considered when using a device beyond its maximum ratings.
8. About the external FET, the parasitic Capacitor may cause the gate voltage to change, when the drain voltage is switching. Make sure to leave adequate margin for this IC variation.
9. On operating Slow Start Control (SS is less than 2.2V), It does not operate Timer Latch.
10. By STB voltage, BD9888F and BD9888FV are changed to 2 states. Therefore, do not input STB pin voltage between one state and the other state (0.8～1.6).
11. The pin connected a connector need to connect to the resistor for electrical surge destruction. This IC is a monolithic IC which (as shown is Fig-1) has P^+ substrate and between the various pins. A P-N junction is formed from this P layer of each pin. For example, the relation between each potential is as follows,
    ○(When GND > PinB and GND > PinA, the P-N junction operates as a parasitic diode.)
    ○(When PinB > GND > PinA, the P-N junction operates as a parasitic transistor.)
    Parasitic diodes can occur inevitably in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits as well as operation faults and physical damage. Accordingly you must not use methods by which parasitic diodes operate, such as applying a voltage that is lower than the GND (P substrate) voltage to an input pin.
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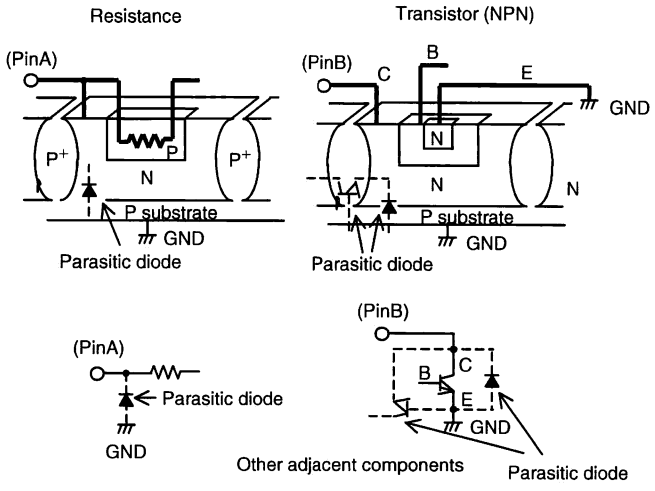

Fig-1 Simplified structure of a Bipolar IC

Notes

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